

1. Description

The PESDR0521P1 is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines.

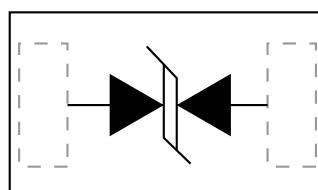
3. Features

- Ultra small package: 1.0x0.6x0.5mm
- Ultra low capacitance: 0.3pF typical
- Ultra low leakage: nA level
- Operating voltage: 5V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 25\text{kV}$
 - Contact discharge: $\pm 22\text{kV}$
 - IEC61000-4-5 (Lightning) 4A (8/20 μs)
- RoHS Compliant

4. Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Video Interface (DVI)
- PCI Express and Serial SATA Ports

5. Pinning information



DFN1006-2



6. Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Units
Peak Pulse Power (8/20 μs)	P_{PK}	100	W
Peak Pulse Current (8/20 μs)	I_{PP}	4	A
ESD per IEC 61000-4-2(Air)	V_{ESD}	± 25	kV
ESD per IEC 61000-4-2(Contact)		± 22	kV
Junction Temperature Range	T_J	-55 to 125	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ\text{C}$

7. Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Reverse Working Voltage	V_{RWM}				5	V
Breakdown Voltage	V_{BR}	$I_T=1\text{mA}$	6.5		9.5	V
Reverse Leakage Current	I_R	$V_{RWM}=5\text{V}$			0.2	μA
Clamping Voltage	V_C	$I_{PP}=1\text{A}$ (8 x 20 μs pulse)			12	V
		$I_{PP}=4\text{A}$ (8 x 20 μs pulse)			25	V
Junction Capacitance	C_J	$V_R=0\text{V}$, $f=1\text{MHz}$		0.3	0.5	pF



8.Typical characteristic

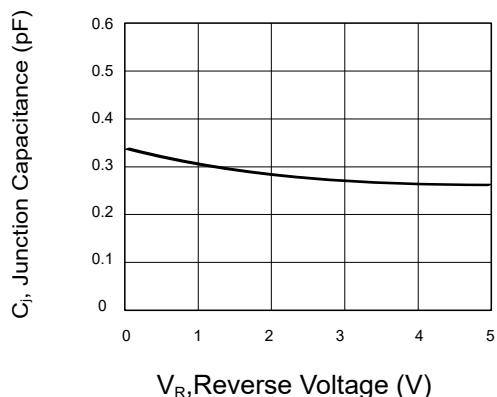


Figure 1: Junction Capacitance vs. Reverse Voltage

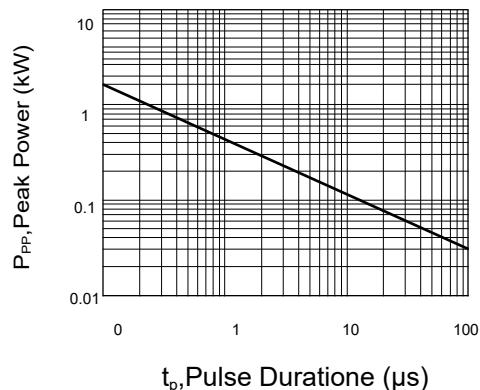


Figure 2: Peak Pulse Power vs. Pulse Time

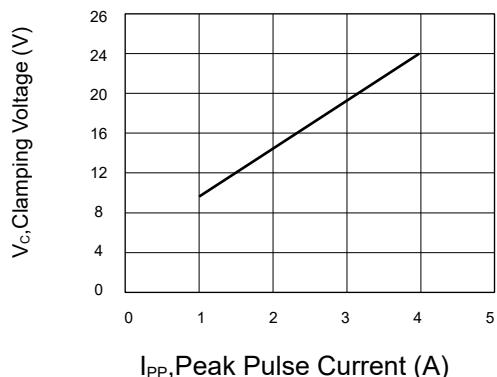


Figure 3: Clamping Voltage vs. Peak Pulse Current

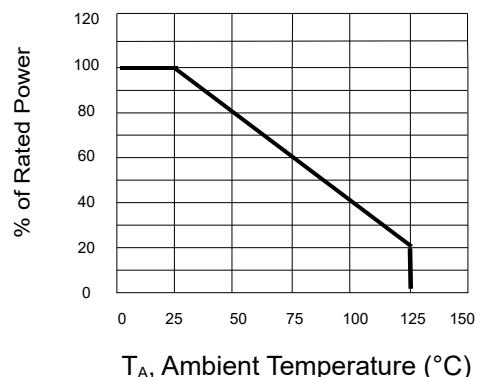


Figure 4: Power Derating Curve

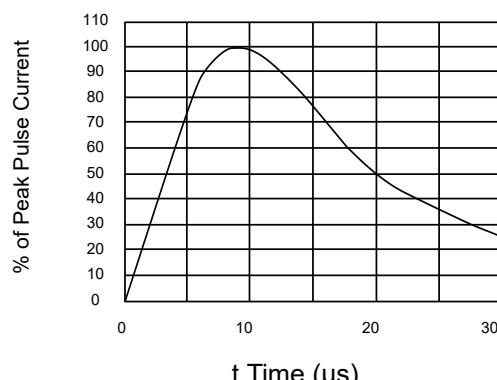


Figure 5: 8 X 20μs Pulse Waveform

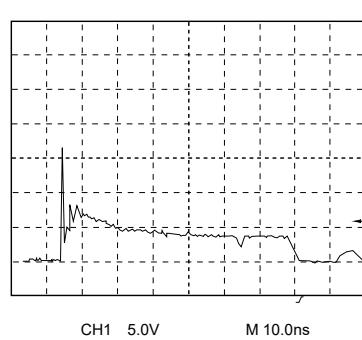
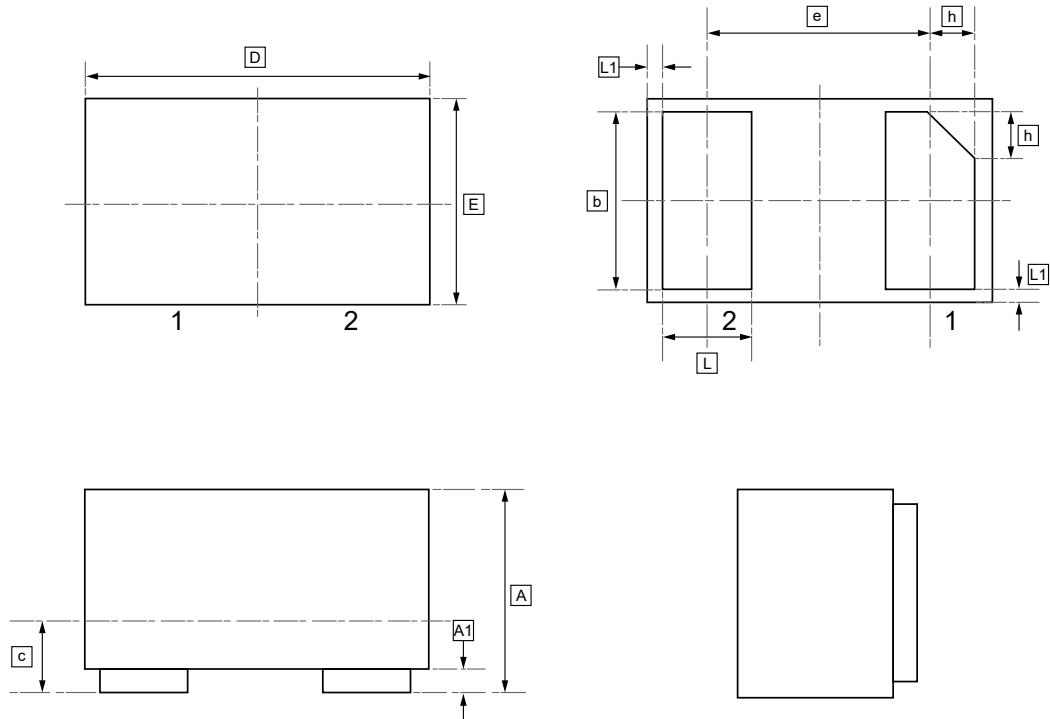


Figure 6: ESD Clamping Voltage 8 kV Contact per IEC61000-4-2



9.DFN1006-2L Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	b	c	D	e	E	L	L1	h
Min	0.45	0.00	0.45	0.12	0.95	0.65	0.55	0.20	0.05	0.07
Max	0.55	0.05	0.55	0.18	1.05	BSC	0.65	0.30	REF	0.17



10.Ordering information

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Order Code	Package	Base QTY	Delivery Mode
UMW PESDR0521P1	DFN1006-2	10000	Tape and reel



11. Disclaimer

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